

Single P-channel MOSFET

ELM58483A-S

<http://www.elm-tech.com>

■ General description

ELM58483A-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■ Features

- $V_{ds} = -100V$
- $I_d = -3.8A$
- $R_{ds(on)} = 260m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} = 290m\Omega$ ($V_{gs} = -4.5V$)

■ Maximum absolute ratings

$T_a = 25^\circ C$. Unless otherwise noted.

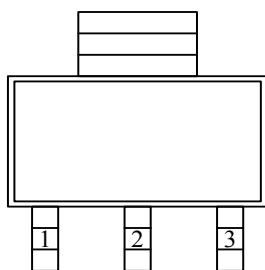
Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{ds}	-100	V
Gate-source voltage	V_{gs}	± 20	V
Continuous drain current	I_d	$T_a = 25^\circ C$	-3.8
		$T_a = 70^\circ C$	-2.6
Pulsed drain current	I_{dm}	-15	A
Power dissipation	P_d	$T_c = 25^\circ C$	2.8
		$T_c = 70^\circ C$	1.2
Operating junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	- 55 to 150	$^\circ C$

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal resistance junction-to-ambient	$R_{\theta ja}$		120	$^\circ C/W$

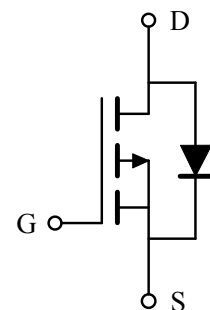
■ Pin configuration

SOT-223(TOP VIEW)



Pin No.	Pin name
1	GATE
2	DRAIN
3	SOURCE

■ Circuit



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■ Electrical characteristics

Ta=25°C. Unless otherwise noted.

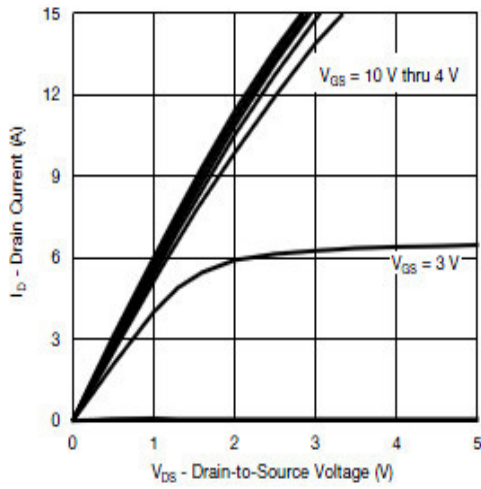
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Vgs=0V, Id=-250μA	-100			V
Zero gate voltage drain current	Idss	Vds=-80V, Vgs=0V			-1	μA
		Vds=-80V, Vgs=0V, Ta=85°C			-30	
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±100	nA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=-250μA	-1.0		-2.5	V
On state drain current	Id(on)	Vgs=-10V, Vds≥-10V	-8			A
Static drain-source on-resistance	Rds(on)	Vgs=-10V, Id=-3.8A		235	260	mΩ
		Vgs=-4.5V, Id=-2.6A		255	290	
Forward transconductance	Gfs	Vds=-15V, Id=-3.2A		12		S
Diode forward voltage	Vsd	Is=-2.0A, Vgs=0V		-0.8	-1.3	V
Max. body-diode continuous current	Is				-5	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss	Vgs=0V, Vds=-50V, f=1MHz		1100		pF
Output capacitance	Coss			70		pF
Reverse transfer capacitance	Crss			45		pF
SWITCHING PARAMETERS						
Total gate charge	Qg	Vgs=-4.5V, Vds=-50V Id=-2.6A		12.0	20.0	nC
Gate-source charge	Qgs			3.0		nC
Gate-drain charge	Qgd			4.5		nC
Turn-on delay time	td(on)	Vgs=-10V, Vds=-50V RL=17Ω, Id=-2.6A Rgen=1.0Ω		8	15	ns
Turn-on rise time	tr			15	20	ns
Turn-off delay time	td(off)			35	50	ns
Turn-off fall time	tf			10	25	ns

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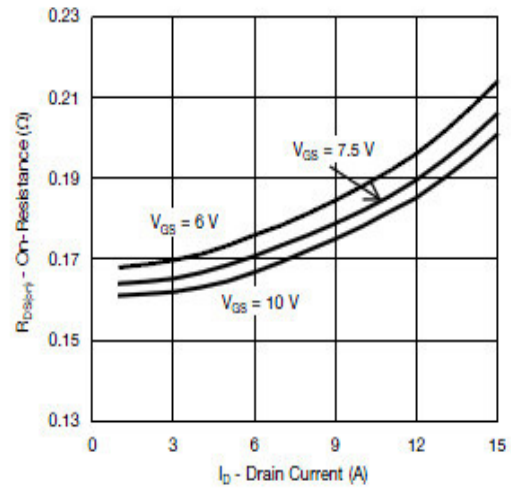
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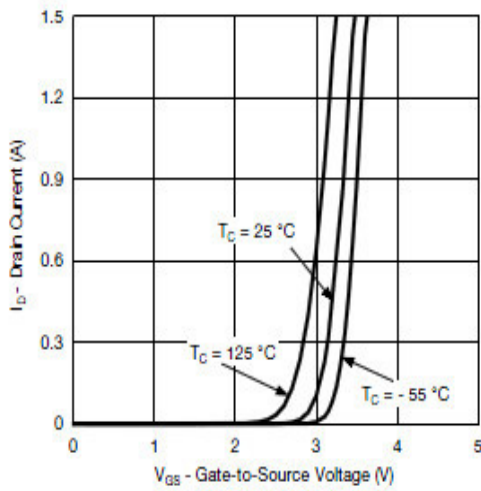
■ Typical electrical and thermal characteristics



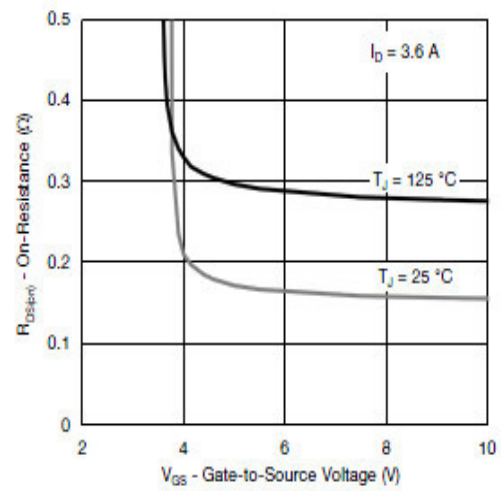
Output Characteristics



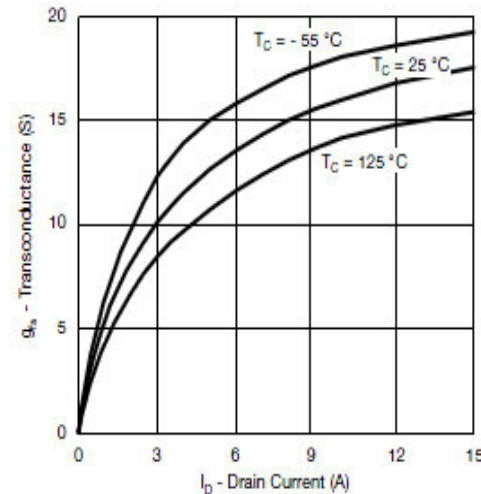
On-Resistance vs. Drain Current



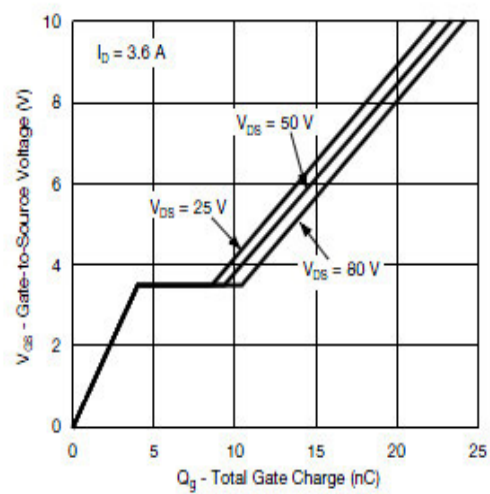
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage



Transconductance

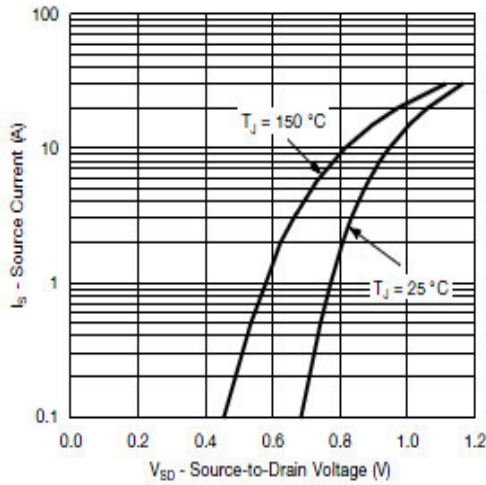


Gate Charge

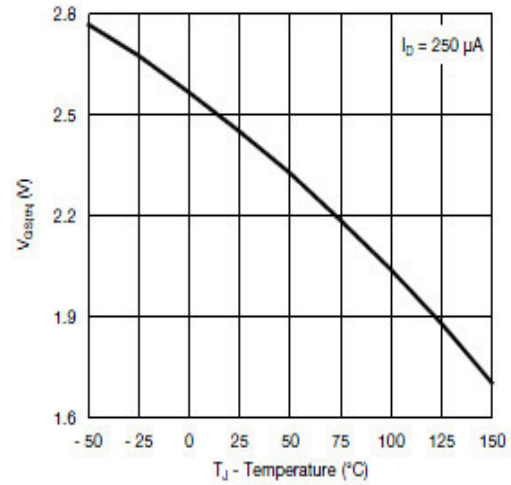
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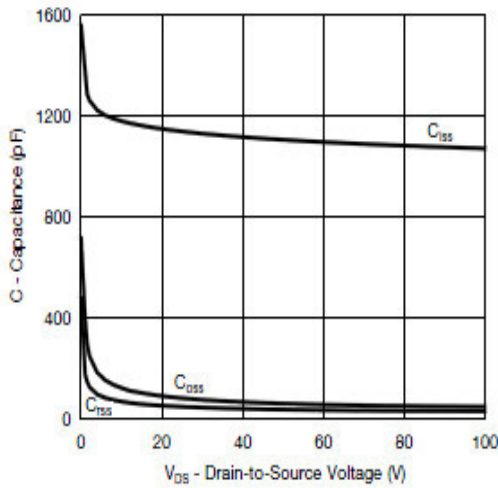
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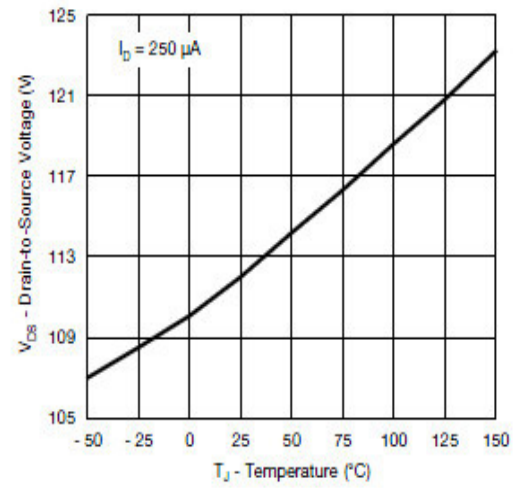
Source-Drain Diode Forward Voltage



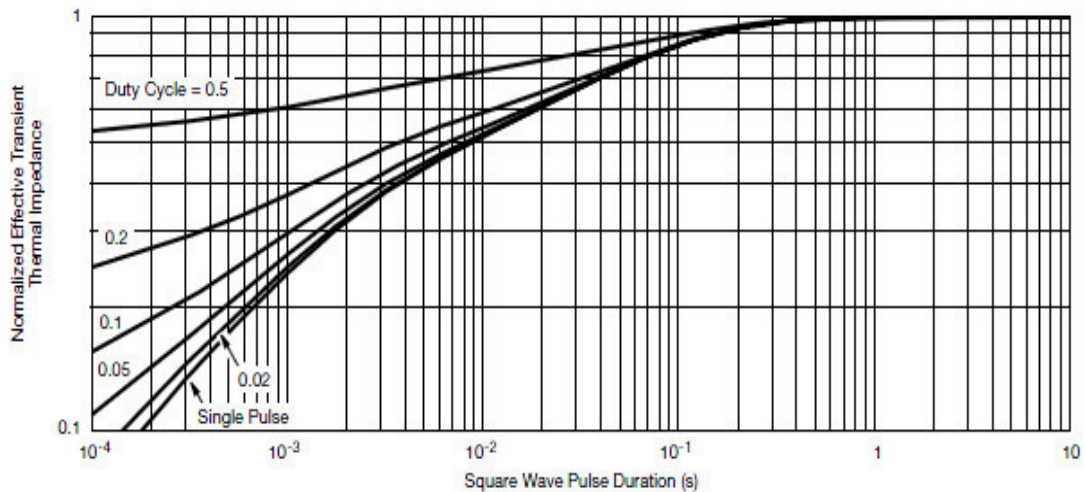
Threshold Voltage



Capacitance



Drain Source Breakdown vs. Junction Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

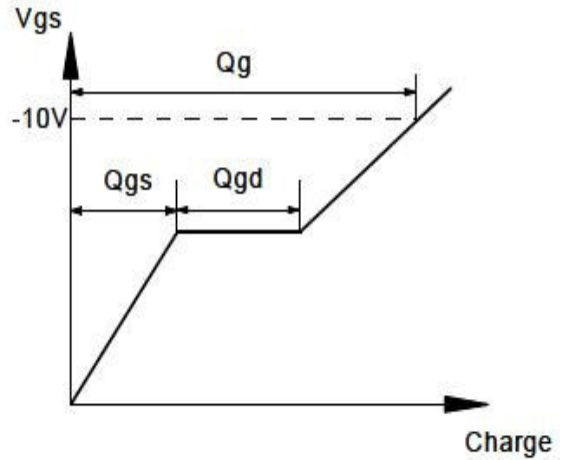
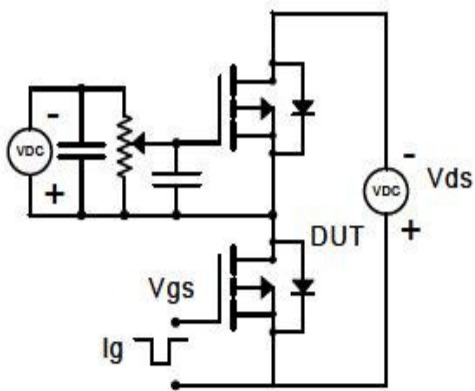
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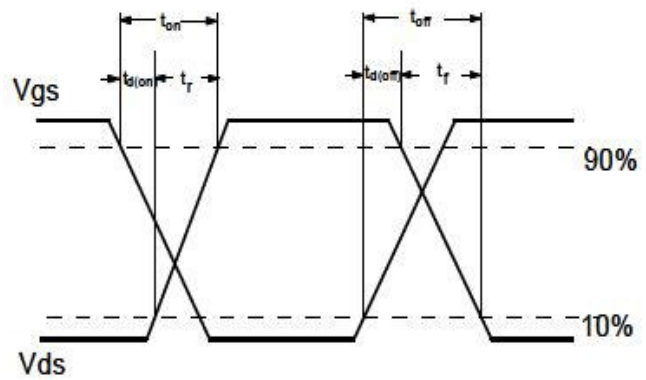
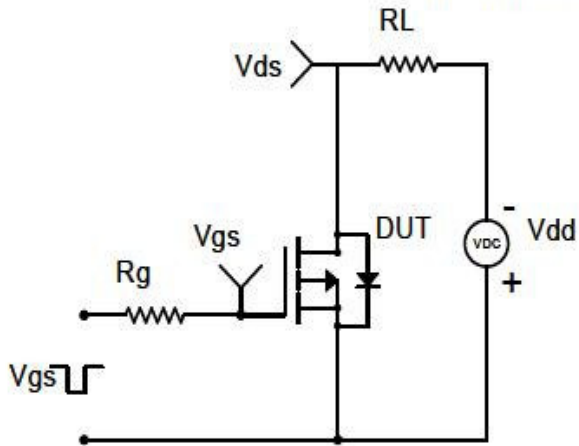
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■ Test circuit and waveform

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

